富满微电子集团股份有限公司 FINE MADE MICROELECTRONICS GROUP CO., LTD. FM8625H (文件编号: S&CIC2082) SPDT Switch for 5G Applications

PRODUCT DESCRIPTION

The FM8625H is a Single-Pole, Double-Throw (SPDT) GSM/LTE/WCDMA/WiFi transmitting and receiving switch. Switching is controlled by an integrated GPIO interface with a single control pin.

The FM8625H SPDT switch is provided in a compact 1.1mm x 0.7mm x 0.5mm 6-lead DFN package which allows for a small solution size with no need for external DC blocking capacitors unless DC is applied externally.

A functional block diagram is shown in Figure 1 and the pin configuration are shown in Figure 2. Signal pin assignments and functional pin descriptions are provided in Table 1.

FEATURES

- Broadband frequency range: 0.1 to 6.0 GHz
- Low insertion loss: 0.45 dB @ 2.7 GHz
- Low insertion loss: 0.65 dB @ 5.8 GHz
- High isolation: 30 dB up to 2.7 GHz
- P0.1dB: 38 dBm
- No external DC blocking capacitors required
- Single GPIO control line with voltage regulator:

 V_{CTL} = 0 to VDD V

 V_{DD} = 1.62 to 3.3 V

 Small, 1.1mm x 0.7mm x 0.5mm 6-lead DFN package

APPLICATIONS

- GSM/WCDMA/LTE transmitting and receiving
- WiFi 2.4G/5G transmitting and receiving
- HPUE applications



Figure 1. FM8625H Block Diagram



Figure 2. FM8625H Pinout (Top View)

富满微电子集团股份有限公司 FINE MADE MICROELECTRONICS GROUP CO., LTD.

FM8625H (文件编号: S&CIC2082) **SPDT Switch for 5G Applications**

FUNCTION CHARACTERISTICS



Figure 3. FM8625H Application Circuit

Table 1. Pin Descriptions

No.	Name	Description	No.	Name	Description
1	RF2	RF Port2	6	VCTL	Logic Control Voltage
2	GND	Ground	5	ANT	Antenna Port
3	RF1	RF Port1	4	VDD	DC Power Supply Voltage

Table 2. VCTL Truth Table for RF Channel Operating Mode

VCTL	RF Channel Operating Mode		
Low	ANT to RF1 active		
High	ANT to RF2 active		



FUNCTION CHARACTERISTICS

Table 3. Absolute Maximum Ratings

Parameter	Symbol	Min	Max	Unit			
DC Supply Voltage	V _{DD}	0	+3.6				
Digital Control Voltage	V _{CTL}	0	+3.0	V			
RF Input Peak Power							
cw	P _{IN}		37				
20% DC	P _{IN}		38	dBm			
Device operating temperature	T _{OP}	-40	+90				
Device storage temperature	T _{STG}	-55	+150	°C			
Electrostatic Discharge							
Human body model (HBM), Class 1C	V _{ESD(HBM)}		1000				
Machine Model (MM), Class A	V _{ESD(MM)}		100	V			
Charged device model (CDM), Class III	V _{ESD(CDM)}		500	v			

Note: Exposure to maximum rating conditions for extended periods may reduce device reliability. There is no damage to device with only one parameter set at the limit and all other parameters set at or below their nominal value. Exceeding any of the limits listed here may result in permanent damage to the device.

Table 4. Recommended Operating Conditions

Parameter	Symbol	MIN	TYP	MAX	Unit
Operating Frequency	Fo	0.1		5.8	GHz
DC Supply Voltage	V _{DD}	1.62	2.8	3.3	
Logic Control Voltage High	V _{CTL_H}	1.62	1.8	VDD	
Logic Control Voltage Low	V _{CTL_L}	0	0	0.3	

富满微电子集团股份有限公司 FINE MADE MICROELECTRONICS GROUP CO., LTD.

FM8625H (文件编号: S&CIC2082) SPDT_Switch for 5G Applications

Table 5. Nominal Operating Parameters

Parameter	r Symbol Specification		Unit	Condition			
		MIN	ТҮР	MAX			
DC Performances							
DC Supply Current	I _{DD}		100	130		V _{DD} = 2.8V	
Current on VCTL	I _{CTL}			5	μΑ	V _{CTL} = 1.8V	
DC Supply Turn-on/Turn-	т			10	μs	From 50% of final VDD voltage to	
off Time	ON/OFF					90%/10% of final RF power	
DE Doth Switching Time	т		2	3	μs	From 50% of final VCTL voltage to	
RF Pain Switching Time	I _{SW}					10%/90% of final RF power	
RF Performances							
			0.30	0.35	- dB	F ₀ =0.1 to 1.0 GHz	
Insertion Loop	IL		0.35	0.45		F ₀ =1.0 to 2.0 GHz	
(PE1 or PE2 to ANT pip)			0.45	0.50		F ₀ =2.0 to 3.0 GHz	
			0.50	0.60		F ₀ =3.0 to 3.8 GHz	
			0.65	0.75		F ₀ =4.8 to 6.0 GHz	
	ISO	35	40			F ₀ =0.1 to 1.0 GHz	
lagistics		32	35			F ₀ =1.0 to 2.0 GHz	
		28	30			F ₀ =2.0 to 3.0 GHz	
		22	25			F ₀ =3.0 to 3.8 GHz	
		18	20			F ₀ =4.8 to 6.0 GHz	
Voltage Standing Wave			1.5			F ₀ =0.1 to 2.7 GHz	
Ratio	VSWR		2.0			$F_0=2.7$ to 6.0 GHz	
Input 0.1dB Compression							
Point (From ANT to RF1	P _{0.1dB}	37	38		dBm	F₀=0.95 to 6.0GHz	
and RF2)							
2nd Harmonic	2F ₀		-75	-65	dDa	F ₀ =900MHz @ 35dBm	
			-85	-75		F ₀ =900MHz @ 26dBm	
3rd Harmonic	3⊑		-75	-65		F₀=900MHz @ 35dBm	
			-85	-75		F₀=900MHz @ 26dBm	